

P-Channel 1.8 V (G-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 20	0.110 at $V_{GS} = - 4.5$ V	- 3.6
	0.160 at $V_{GS} = - 2.5$ V	- 3.0
	0.240 at $V_{GS} = - 1.8$ V	- 2.4

SCHOTTKY PRODUCT SUMMARY		
V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A)
20	0.375 V at 1 A	1.0

FEATURES

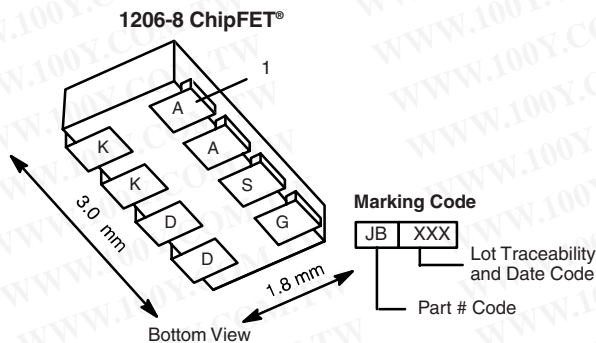
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Ultra Low V_f Schottky
- Si5853DC Pin Compatible
- Compliant to RoHS Directive 2002/95/EC



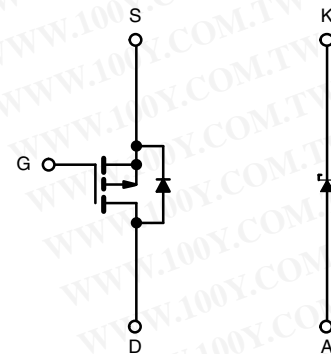
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Charging Circuit in Portable Devices



Ordering Information: Si5855DC-T1-E3 (Lead (Pb)-free)
Si5855DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage (MOSFET)	V_{DS}	- 20		V	
Reverse Voltage (Schottky)	V_{KA}	20			
Gate-Source Voltage (MOSFET)	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) (MOSFET) ^a	I_D	$T_A = 25^\circ\text{C}$	- 3.6	- 2.7	
		$T_A = 85^\circ\text{C}$	- 2.6	- 1.9	
Pulsed Drain Current (MOSFET)	I_{DM}	- 10		A	
Continuous Source Current (MOSFET Diode Conduction) ^a	I_S	- 1.8	- 0.9		
Average Forward Current (Schottky)	I_F	1.0			
Pulsed Forward Current (Schottky)	I_{FM}	7		W	
Maximum Power Dissipation (MOSFET) ^a	P_D	$T_A = 25^\circ\text{C}$	2.1		1.1
		$T_A = 85^\circ\text{C}$	1.1		0.6
Maximum Power Dissipation (Schottky) ^a	P_D	$T_A = 25^\circ\text{C}$	1.9		1.1
		$T_A = 85^\circ\text{C}$	1.0		0.56
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature) ^{b, c}		260			

Notes:

- Surface mounted on 1" x 1" FR4 board.
- See reliability manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

THERMAL RESISTANCE RATINGS

Parameter	Device	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	t ≤ 5 s	MOSFET	50	60	°C/W
		Schottky	54	65	
	Steady State	MOSFET	90	110	
		Schottky	95	115	
Junction-to-Foot	Steady State	MOSFET	30	40	
		Schottky	30	40	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS T_J = 25 °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45		-1.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V, I _D = -2.7 A		0.095	0.110	Ω
		V _{GS} = -2.5 V, I _D = -2.2 A		0.137	0.160	
		V _{GS} = -1.8 V, I _D = -1 A		0.205	0.240	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -2.7 A		7		S
Diode Forward Voltage ^a	V _{SD}	I _S = -0.9 A, V _{GS} = 0 V		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -2.7 A		5.1	7.7	nC
Gate-Source Charge	Q _{gs}			1.2		
Gate-Drain Charge	Q _{gd}			1.0		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -10 V, R _L = 10 Ω I _D ≡ -1 A, V _{GEN} = -4.5 V, R _g = 6 Ω		16	25	ns
Rise Time	t _r			30	45	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			27	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = -0.9 A, di/dt = 100 A/μs		20	40	

Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

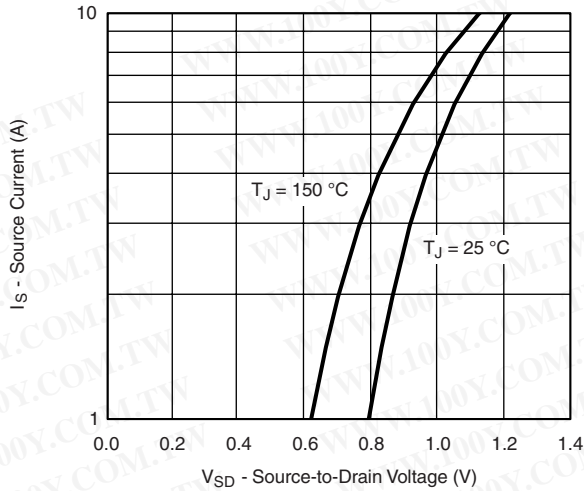
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

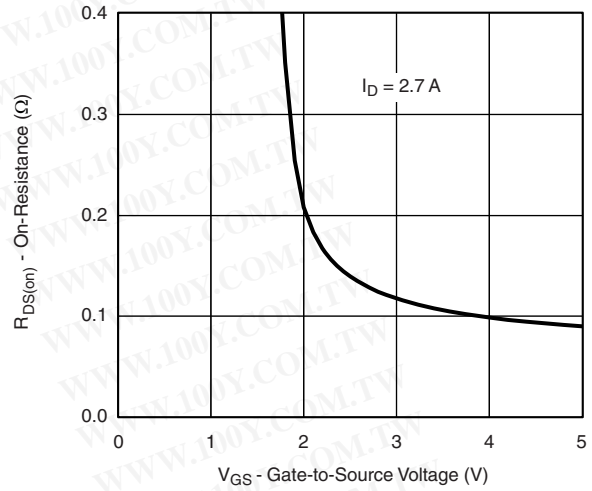
SCHOTTKY SPECIFICATIONS T_J = 25 °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V _F	I _F = 1 A		0.34	0.375	V
		I _F = 1 A, T _J = 125 °C		0.255	0.290	
Maximum Reverse Leakage Current	I _{rm}	V _r = 20 V		0.05	0.500	mA
		V _r = 20 V, T _J = 85 °C		2	20	
		V _r = 20 V, T _J = 125 °C		10	100	
Junction Capacitance	C _T	V _r = 10 V		90		pF

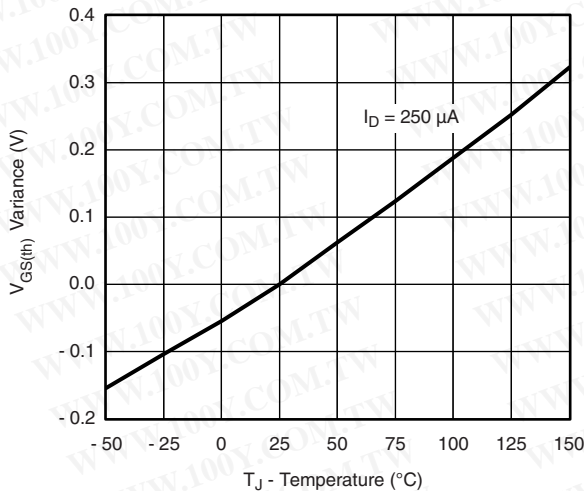
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



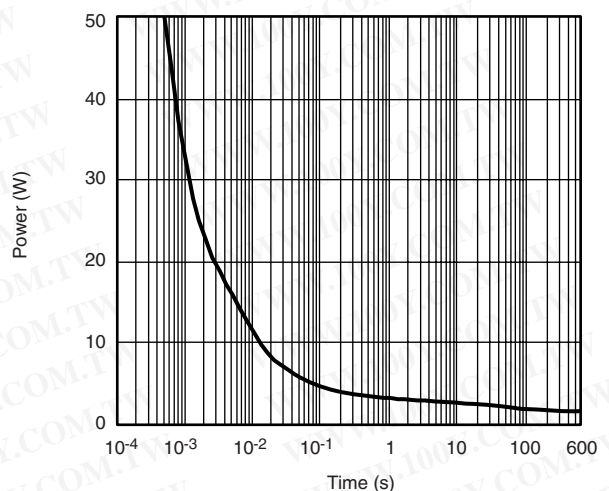
Source-Drain Diode Forward Voltage



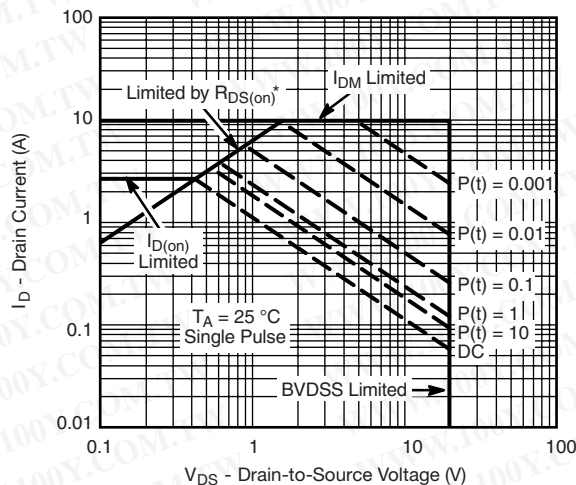
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



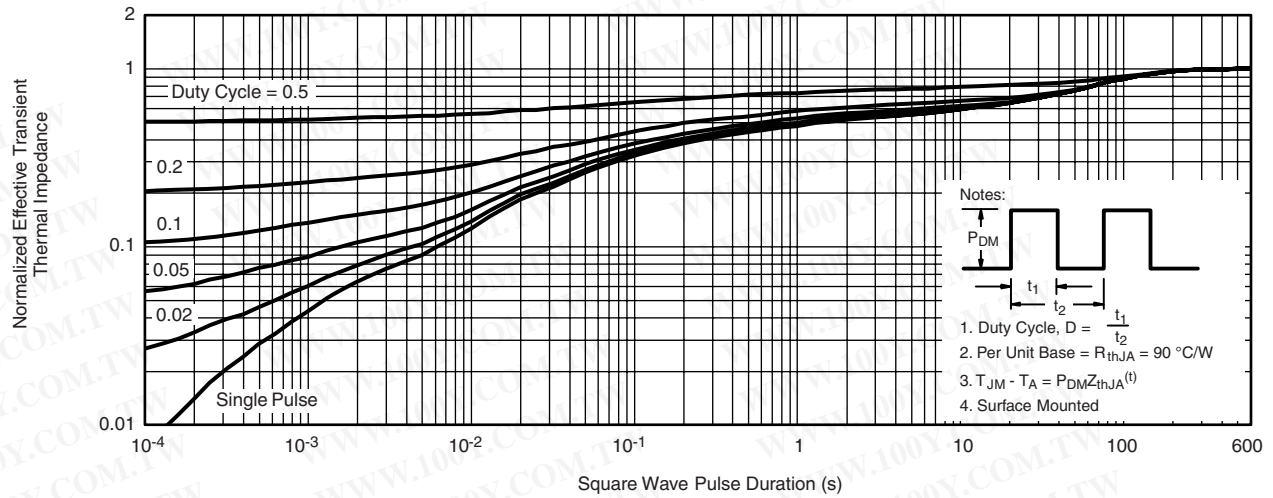
Single Pulse Power



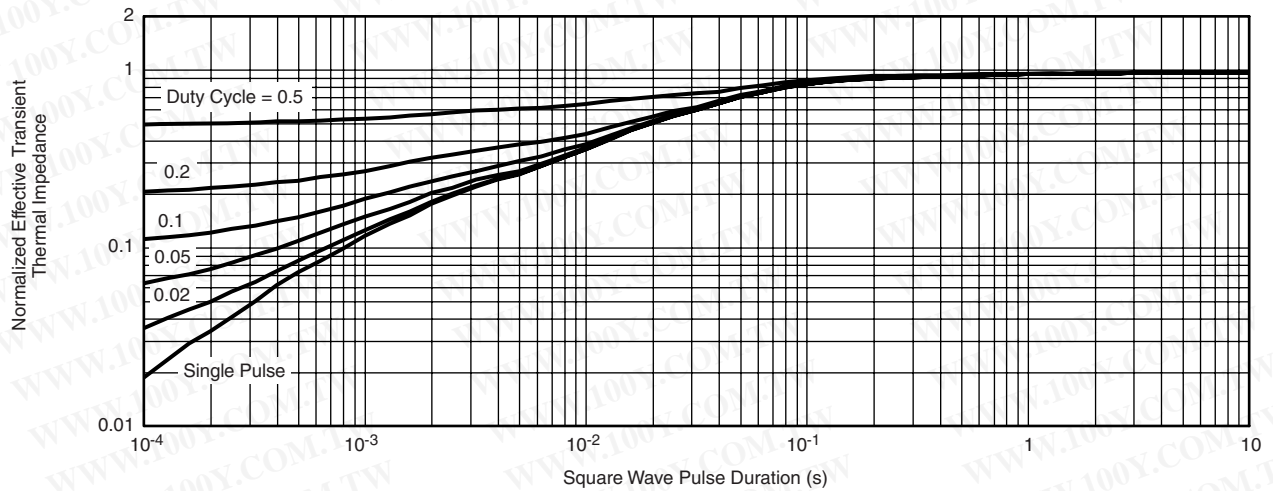
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

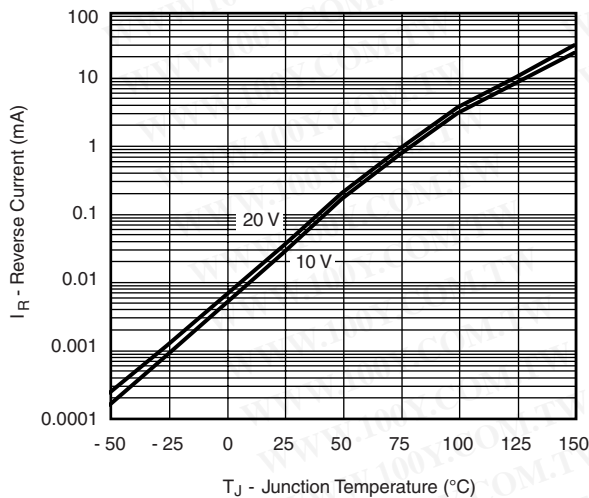


Normalized Thermal Transient Impedance, Junction-to-Ambient

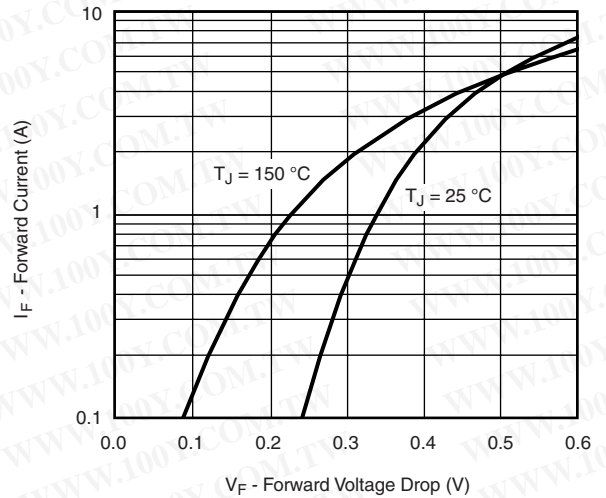


Normalized Thermal Transient Impedance, Junction-to-Foot

SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



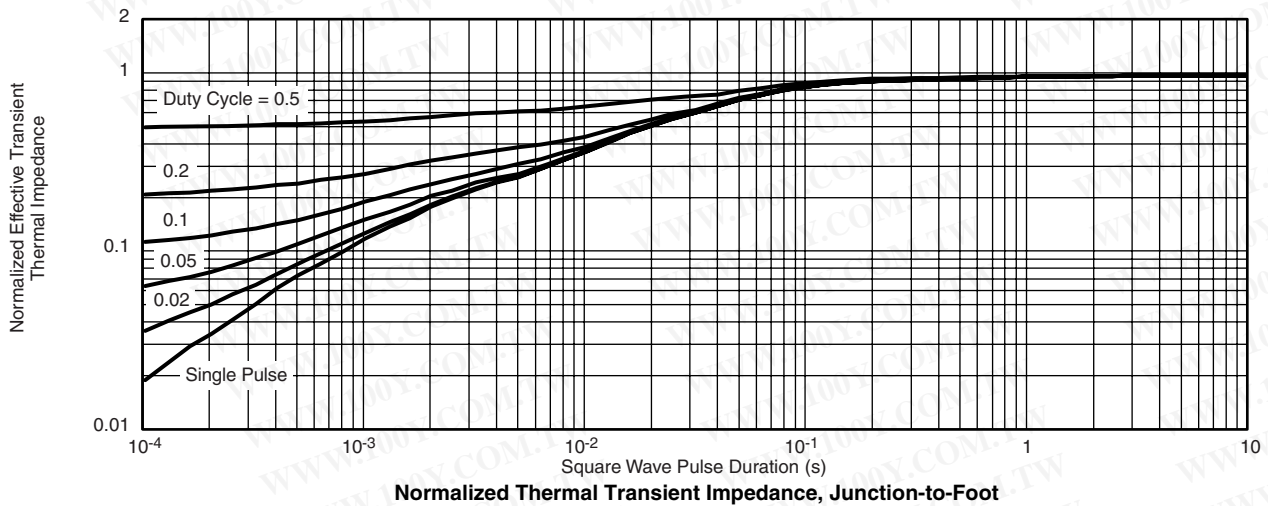
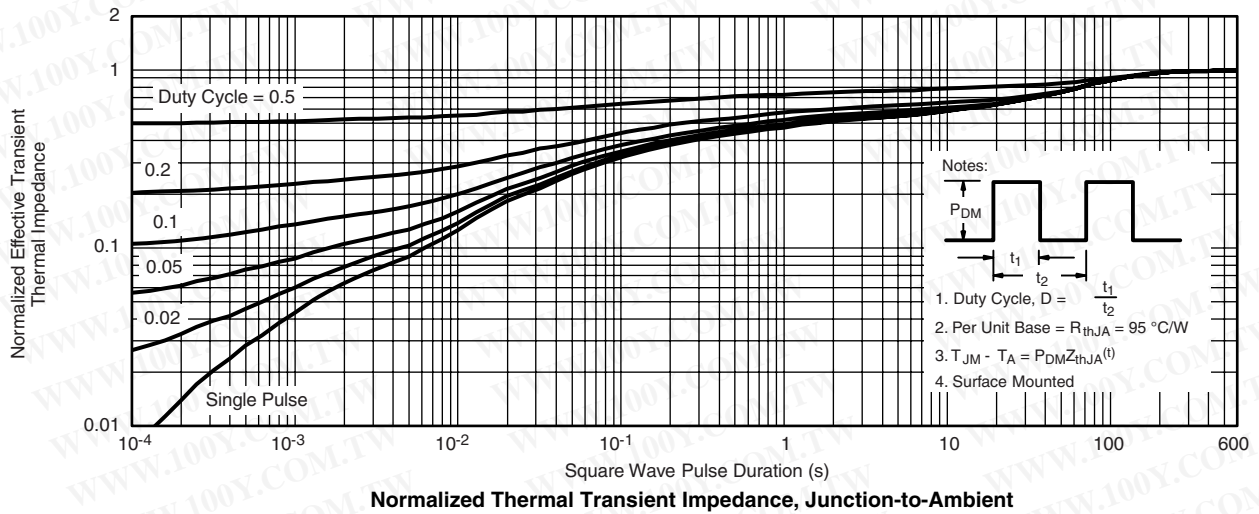
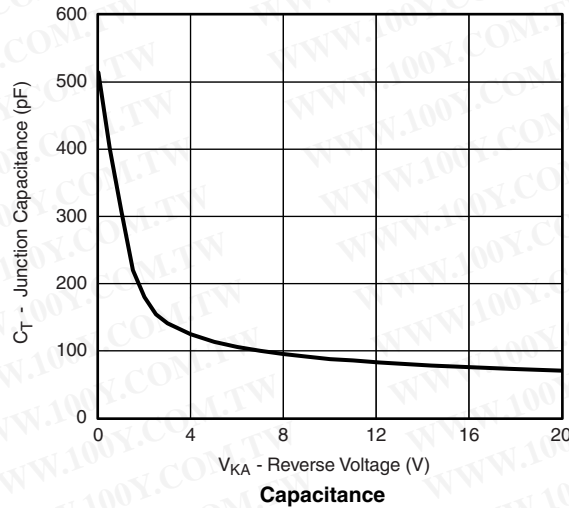
Reverse Current vs. Junction Temperature



Forward Voltage Drop



SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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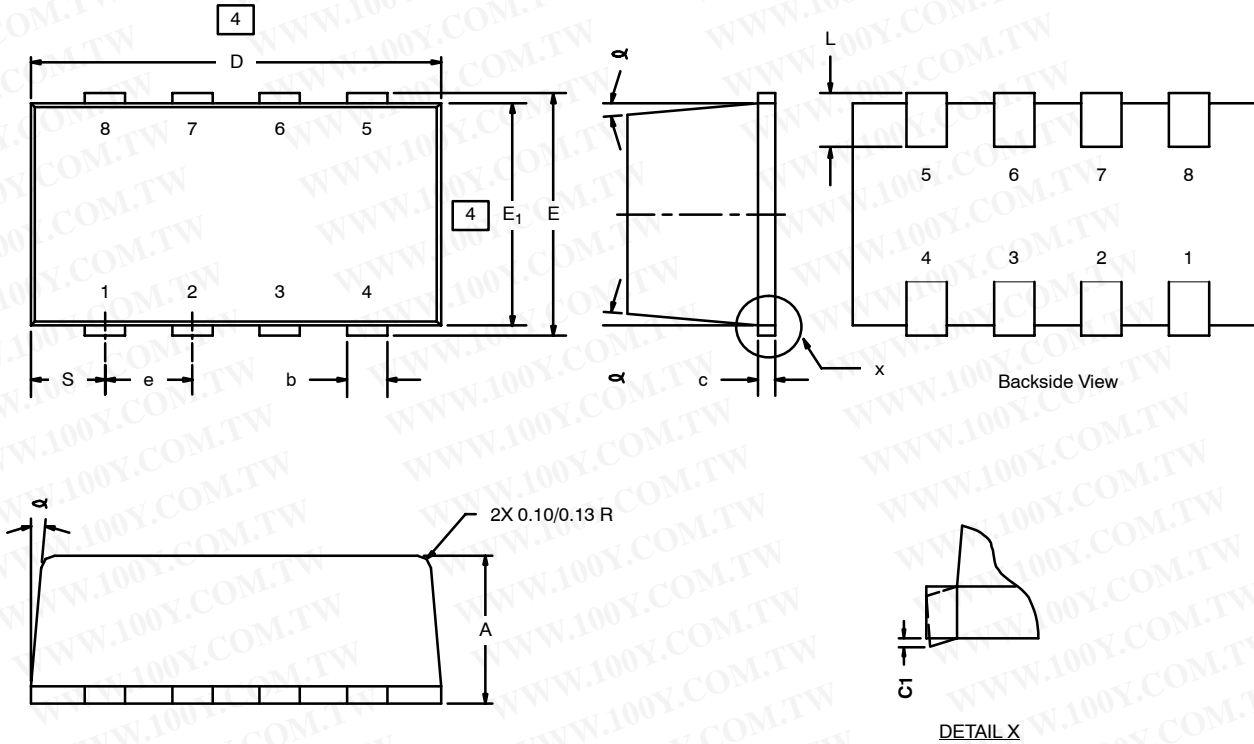


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Package Information

Vishay Siliconix

1206-8 ChipFET®

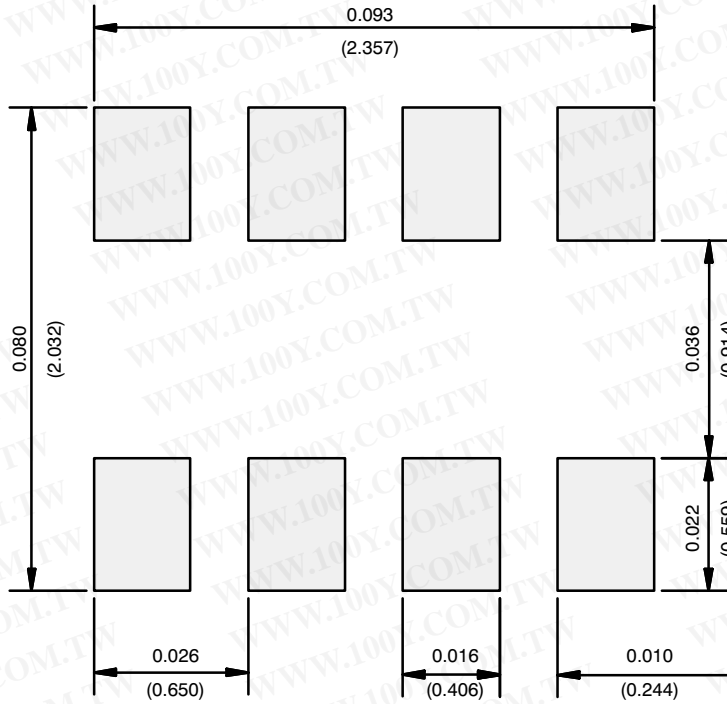


NOTES:

- All dimensions are in millimeters.
- Mold gate burrs shall not exceed 0.13 mm per side.
- Leadframe to molded body offset is horizontal and vertical shall not exceed 0.08 mm.
- Dimensions exclusive of mold gate burrs.
- No mold flash allowed on the top and bottom lead surface.

Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	1.00	-	1.10	0.039	-	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.1	0.15	0.20	0.004	0.006	0.008
c1	0	-	0.038	0	-	0.0015
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.825	1.90	1.975	0.072	0.075	0.078
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.0256 BSC		
L	0.28	-	0.42	0.011	-	0.017
S	0.55 BSC			0.022 BSC		
alpha	5°Nom			5°Nom		
ECN: C-03528—Rev. F, 19-Jan-04 DWG: 5547						

RECOMMENDED MINIMUM PADS FOR 1206-8 ChipFET®



Recommended Minimum Pads
Dimensions in Inches/(mm)

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